# GenISys Layout LAB

**All in One Lithography Simulation**

**Equipment Training**
Please contact Alan Bleier or Amrita Banerjee for training.

## Description:

Lithography simulation enables virtual exploration of a huge parameter space in little time. The fast and accurate calculation of the intensity image enables layout optimization (OPC), mask layout verification, optimization of process conditions (e.g. illumination, stack) and process window (e.g. gap or defocus and exposure dose variation) by varying layout and/or exposure parameters. Thousands of experiments can be computed “overnight” without producing masks or “burning” wafers.

## Capabilities:

- VisualFLOWTM graphical user interface for drag & drop design of process flows
- Import, Export of all major layout for mats (GDSII, CIF, DXF)
- LayoutEditor
- Mask Definition
- Stack Definition
- Proximity Exposure
- Projection Exposure
- Electron Beam Exposure
- Resist Development

## Documentation:

- Quick Start Guide (PDF)
- Manual
- Training Videos

## Invoking:

On the CNF conversion computers, the current version of GenISys LayoutLAB can be invoked with any of the following commands (don't type in the dollar sign, that is the command prompt):

```
$ lab
```